

2SA2028

Silicon PNP epitaxial planer type

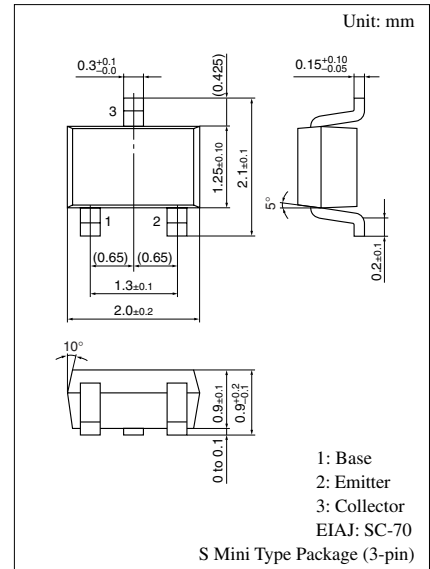
For DC-DC converter

■ Features

- Large current capacitance
- Low collector to emitter saturation voltage
- High-speed switching
- Small type package, allowing downsizing and thinning of the equipment.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	-20	V
Collector to emitter voltage	V_{CEO}	-20	V
Emitter to base voltage	V_{EBO}	-5	V
Peak collector current	I_{CP}	-3	A
Collector current	I_C	-1	A
Collector power dissipation	P_C	150	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$



Marking Symbol: AT

■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector to base voltage	V_{CBO}	$I_C = -10 \mu\text{A}$, $I_E = 0$	-20			V
Collector to emitter voltage	V_{CEO}	$I_C = -1 \text{ mA}$, $I_B = 0$	-20			V
Emitter to base voltage	V_{EBO}	$I_E = -10 \mu\text{A}$, $I_C = 0$	-5			V
Forward current transfer ratio *	h_{FE}	$V_{CE} = -2 \text{ V}$, $I_C = -100 \text{ mA}$	160		560	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = -200 \text{ mA}$, $I_B = -10 \text{ mA}$		-40	-100	mV
Collector output capacitance	C_{ob}	$V_{CB} = -10 \text{ V}$, $I_E = 0$, $f = 1 \text{ MHz}$		20	30	pF
Transition frequency	f_T	$V_{CB} = -10 \text{ V}$, $I_E = 10 \text{ mA}$ $f=200 \text{ MHz}$		170		MHz